



IRFB3207PBF Information

Part Number IRFB3207PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 75V 180A TO-220AB

TO-220-3 **Package**

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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IRFB3207PBF Specifications

Manufacturer Part NumberIRFB3207PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C170A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs260nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 75V Current - Continuous Drain (Id) @ 25°C 170A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 260nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 50V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 330W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer Part Number	IRFB3207PBF
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SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75 VCurrent - Continuous Drain (Id) @ 25°C170A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs260nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 50 VVgs (Max)±20 VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10 VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C170A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs260nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C170A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs260nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	HEXFET?
Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C170A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs260nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7600pF @ 50VVgs (Max)±20VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature Supplier Device Package Package / Case 170A (Tc)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Australiance (Tiss) (Max) Operating Temperature Supplier Device Package Package / Case 10V 400 P	Drain to Source Voltage (Vdss)	75V
Vgs(th) (Max) @ Id	Current - Continuous Drain (Id) @ 25°C	170A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 7600pF @ 50V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature Coperating Temperature John Coperating Tem	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)330W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	260nC @ 10V
FET Feature - Power Dissipation (Max) 330W (Tc) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	7600pF @ 50V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	330W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	4.5 mOhm @ 75A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRFB3207PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFB3207PBF Payment Methods





















IRFB3207PBF Shipping Methods













If you have any question about IRFB3207PBF, please do not hesitate to contact us!

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